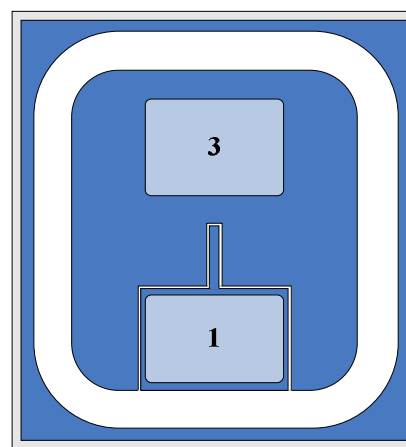


3VD182600YL HIGH VOLTAGE MOSFET CHIPS

DESCRIPTION

- Ø 3VD182600YL is a High voltage N-Channel enhancement mode power MOS-FET chip fabricated in advanced silicon epitaxial planar technology.
- Ø Advanced termination scheme to provide enhanced voltage-blocking capability.
- Ø Avalanche Energy Specified
- Ø Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Ø The chips may packaged in TO-92DT-3L type and the typical equivalent product is 1N60C.
- Ø The packaged product is widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.
- Ø Die size: 1.90mm*1.75mm.
- Ø Chip Thickness: 300±20μm.
- Ø Top metal : Al, Backside Metal : Ag.



PAD1:GATE PAD3:SOURCE

CHIP TOPOGRAPHY

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25°C)

Parameter	Symbol	Ratings	Unit
Drain-Source voltage	VDS	600	V
Gate-Source Voltage	VGS	±30	V
Drain Current	ID	800	mA
Operation Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V(BR)DSS	ID=250uA	600	---	----	V
Gate-Threshold Voltage	Vth(GS)	ID=250uA VDS=VGS	2	---	4	V
Gate-body Leakage	IGSS	VGS=±30V, VDS=0V	---	---	±100	nA
Zero Gate Voltage Drain Current	IDSS	VDS=600V, VGS=0V	---	---	1	μA
Drain-Source On-Resistance	RDS(on)	ID=0.5A, VGS=10V	---	---	12	Ω
Source-Drain Diode Forward on Voltage	VFSD	ID=1.0A, VGS=0V	---	---	1.50	V